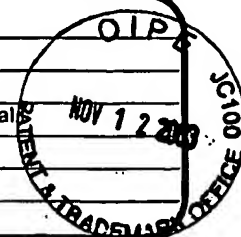


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Substitute for form 1448A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Complete if Known	
		Application Number	10/086,621
		Filing Date	March 4, 2002
		First Named Inventor	Valery KAGADEI, et al
		Group Art Unit	2838
		Confirmation No.	6897
Sheet 1	of 2	Attorney Docket Number	KAGADEI=1



OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
KF	BB	ANISHCHENKO et al., <i>Dry Cleaning of Fluorocarbon Residues by Atomic Hydrogen Flow</i> , International Conference Micro- and Nanoelectronic, ICMN-2003, (October, 2003), pp. 1-6.	
	BC	ANISHCHENKO et al., <i>Residual Photoresist Removal from Si and GaAs Surface by Atomic Hydrogen Flow Treatment</i> , International Conference Micro- and Nanoelectronic, ICMN-2003, (October, 2003), pp. 1-5.	
	BD	BOZHKOV et al., <i>A Comparative Study of the Atomic Hydrogen Penetration into the Thin Vanadium Films and Silicon Oxide-Gallium Arsenide Structures</i> , Technical Physics Letters, Vol. 26, no. 10 (2000), pp. 926-928.	
	BE	CHALDYSHEV et al, <i>Hydrogenation of GaAs Films Grown at Low Temperature</i> , Symposium on Non-Stoichiometric III-V Compounds, (October, 2001), pp. 1-6.	
	BF	KAGADEI et al, <i>Atomic Hydrogen Flux Density Measured Using Thin Metal Films</i> , Technical Physics Letters, Vol. 29, no. 11 (2003), pp. 897-900.	
	BG	KAGADEI et al, <i>Current-Voltage Characteristics of a Reflex Discharge with a Hollow Cathode and Self-Heating Electrode</i> , Technical Physics, Vol. 46, no. 3 (2001), pp. 292-298. <i>Published in Mar 01</i>	
	BH	KAGADEI et al, <i>The Effect of Atomic Hydrogen Flow on Electrical Resistance of the Transition Metal Films</i> , The European Material Conference, E-MRS, (June, 2003), pp. 1-15.	
	BI	KAGADEI et al, <i>The Effect of Hydrogenation on the Photoconductivity of Ion-Doped Gallium Arsenide Structures</i> , Technical Physics Letters, Vol. 26, no. 4 (2000), pp. 269-271.	
	BJ	KAGADEI et al, <i>The Effect of Hydrogenation on the Sink Breakdown Voltage of Transistors Based on Ion-Doped Gallium Arsenide Structures</i> , Technical Physics Letters, Vol. 29, no. 1 (2003), pp. 12-15.	
	BK	KAGADEI et al, <i>Hydrogenation Kinetics and Change in Resistance of Thin Vanadium Films Under Treatment by Atomic Hydrogen Flow</i> , Izvestiya Vysshikh Uchebykh Zavedenii, Fizika, no. 11 (2003), pp. 67-76. <i>(Abstract only)</i>	YES
	BL	KAGADEI et al, <i>In situ Cleaning of GaAs and Al<sub>1-x</sub>Ga<sub>x</sub>As Surfaces and Production of Ohmic Contacts using an Atomic Hydrogen Source Based on a Reflected Arc Discharge</i> , Journal of Vacuum Technology, Vol. 17 (1999), pp. 1488-1493.	
KF	BM	KAGADEI et al, <i>Investigation of the Penetration of Atomic Hydrogen from the Gas Phase into SiO<sub>2</sub>/GaAs</i> , Journal of Vacuum Technology, Vol. 19 (2001), pp. 1871-1877	

Examiner Signature	<i>[Signature]</i>	Date Considered	2-17-04
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Substitute for form 1449A/PTO

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# **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet 2

of 3

## Complete if Known

Application Number	10/086,621
Filing Date	March 4, 2002
First Named Inventor	V. KAGADEI et al.
Group Art Unit	
Examiner Name	
Attorney Docket Number	KAGADEI=1

## OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
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	AK	WOLAN et al., "Chemical reactions induced by the room temperature interaction of hyperthermal atomic hydrogen with the native oxide layer on GaAs(001) surfaces studied by ion scattering spectroscopy and X-ray photoelectron spectroscopy", <u>J. Vac. Sci. Technol.</u> , (1997), vol. 15, No. 5, pages 2502-2507	
	AL	KORZEC et al., "Characterization of a slot antenna microwave plasma source for hydrogen plasma cleaning", <u>J. Vac. Sci. Technol.</u> , (1995), vol. 13, No. 4, page 2074-2085	
	AM	EPI MBE Production Group. Aug./Sept., 1994, Applications Note, "On the Use of Atomic Hydrogen in MBE"	
KE	AN	Application Note, "Cracking Efficiency of the EPI Atomic Hydrogen Source", EPI, January, 1996, No. 1/96	

Examiner Signature

KE

Date Considered

2-17-04

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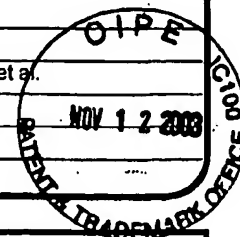
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	10/086,621
		Filing Date	March 4, 2002
		First Named Inventor	Valery KAGADEI, et al.
		Group Art Unit	2838
		Confirmation No.	6897
Sheet	2	of	2
		Attorney Docket Number	KAGADEI=1




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KE	BN	KAGADEI et al, <i>Modeling Atomic Hydrogen Diffusion in GaAs</i> , International Conference Micro- and Nanoelectric, ICMN, (October, 2003), pp. 1-5.	
	BO	KAGADEI et al, <i>Simulation of the Production of Atomic Hydrogen in a Low-Pressure-Arc-Discharge-Based Source</i> , <i>Journal of Vacuum Technology</i> , Vol. 19 (2001), pp. 1346-1352.	
	BP	KAGADEI et al, <i>Suppression of Parasitic Backgating by Hydrogenation of Ion-Doped Gallium Arsenide Structures</i> , <i>Technical Physics Letters</i> , Vol. 25, no. 7 (July, 1999), pp. 522-523.	
	BQ	KAGADEI et al, <i>Use of a New Type of Atomic Hydrogen Source for Cleaning and Hydrogenation of Compound Semiconductive Materials</i> , <i>Journal of Vacuum Technology</i> , Vol. 16 (1998), pp. 2556-2561.	
	BR	Semenov et al, <i>Gas-Discharge Sources with Charged-Particle Emission from the Plasma of a Hollow-Cathode Glow Discharge</i> , <i>Russian Physics Journal</i> , Vol. 44, no. 9 (2001), pp. 977-986.	
	BS	Soltanovich et al., <i>Study of Depth Distribution of Metastable Hydrogen-related defects in n-type GaAs</i> , <i>Physica B: Condensed Matter</i> , Vol. 308-310 (July, 2001), pp. 827-830.	
KE	BT	Tarasenko et al., <i>Application of KrCl excilamp for cleaning GaAs surface using atomic hydrogen</i> , <i>SPIE</i> , Vol. 3274, pp. 323-330.	

Examiner Signature		Date Considered	2-17-04
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)		Compleat if Known	
		Application Number	10/086,621
		Filing Date	March 4, 2002
		First Named Inventor	V. KAGADEI et al.
		Group Art Unit	
Examiner Name		Attorney Docket Number	KAGADEI=1
Sheet	3	of	3

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RF	AO	LIVSHITS et al., "Dissociation of hydrogen molecules on Metal filaments in H <sup>+</sup> ion sources", <u>Plasma Source Sci. Technol.</u> , (1994), pages 465-472	
	AP	HOFLUND et al., "Performance Characteristics of a hyperthermal oxygen-atom generator", <u>Meas. Sci. Technol.</u> , (1994), vol 5, pages 201-204	
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	AR	GEDDES et al., "Dissociation for hydrogen in High frequency discharges", <u>Plasma Source Sci. Technol.</u> , (1993), vol. 2, pages 93-99	
	AS	RF Gas Cracker/Reactive Atom Source - HD Series, The product of Oxford Applied Research	
	AT	GOODMAN et al., "Ar, N <sub>2</sub> , and Cl <sub>2</sub> electron cyclotron resonance plasma measured by time-of-flight analysis: Neutral kinetic energies and source gas cracking", <u>J. Vac. Sci. Technol.</u> , (1997), B vol. 15, No. 4, pages 971-982	
	AU	SHERMAN, "In Situ removal of native oxide from silicon wafers", <u>J. Vac. Sci. Technol.</u> , B vol. 8, No. 4, pages 656-657	
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	AY	Handbook of Ion Sources, Ed. by Bernard Wolf, CRC Press, (1995), Pages 32-34, 54-56, 61, 69-71, 222-223	
	AZ	GABOVICH et al., "Out of plasma with high concentration of concentration of charged particles into vacuum", <u>Journal of Technical Physics</u> , (1961), vol. 31, No. 9, Pages 1049-1055	XXX
RF	BA	ITO et al., "Purification of diamond films by applying current into the plasma stream in the arc discharge plasma jet chemical vapor deposition technique", <u>J. Appl. Phys.</u> , (1995), vol. 77, No. 12, Pages 6636-6640	

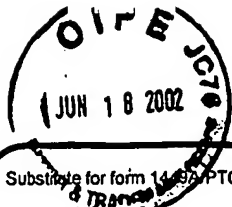
Examiner Signature		Date Considered	<div style="text-align: center;">  </div>
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Substitute for form 14-97 PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)		Complete if Known	
		Application Number	10/086,621
		Filing Date	March 4, 2002
		First Named Inventor	V. KAGADEI et al.
		Group Art Unit	
		Examiner Name	
Sheet	2	of	3
		Attorney Docket Number	KAGADEI=1

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Examiner Signature		Date Considered	2-17-04
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PTO/SB/57 (10/98)

Substitute for form 1449, PTO

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

## Complete if Known

Application Number	10/086,621
Filing Date	March 4, 2002
First Named Inventor	V. KAGADEI et al.
Group Art Unit	
Examiner Name	
Attorney Docket Number	KAGADEI=1

Sheet 3 of 3

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Substitute for form 1449A/ETC

Sheet	1	of	3
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Filing Date	March 4, 2002
First Named Inventor	V. KAGADEI et al.
Group Art Unit	
Examiner Name	
Attorney Docket Number	KAGADEI=1

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$$2-11-04$$

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